Silicon NPN Power Transistors KTC3229

DESCRIPTION

·With TO-220F package

·High voltage :V_{CEO}=300V

APPLICATIONS

·For color TV chroma output application

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

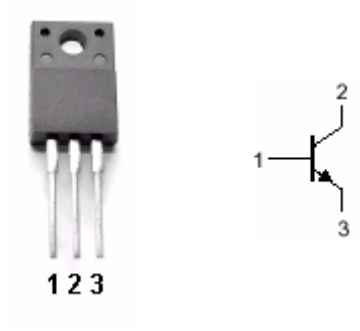

Fig.1 simplified outline (TO-220F) and symbol

Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	300	V
V_{CEO}	Collector-emitter voltage	Open base	300	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		0.1	A
I_B	Base current		20	mA
P_C	Collector dissipation	T_a=25□	2	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V_{CEsat}	Collector-emitter saturation voltage	I_C=10mA; I_B=1mA			1.0	V
I_{CBO}	Collector cut-off current	V_{CB}=240V; I_E=0			1.0	μA
I_{EBO}	Emitter cut-off current	V_{EB}=5V; I_C=0			1.0	μA
h_{FE-1}	DC current gain	I_C=0.5mA ; V_{CE}=10V	20			
h_{FE-2}	DC current gain	I_C=20mA ; V_{CE}=10V	30		200	
f_T	Transition frequency	I_C=20mA ; V_{CE}=20V	75			MHz
C_{OB}	Collector output capacitance	f=1MHz;V_{CB}=20V			4.0	pF

PACKAGE OUTLINE

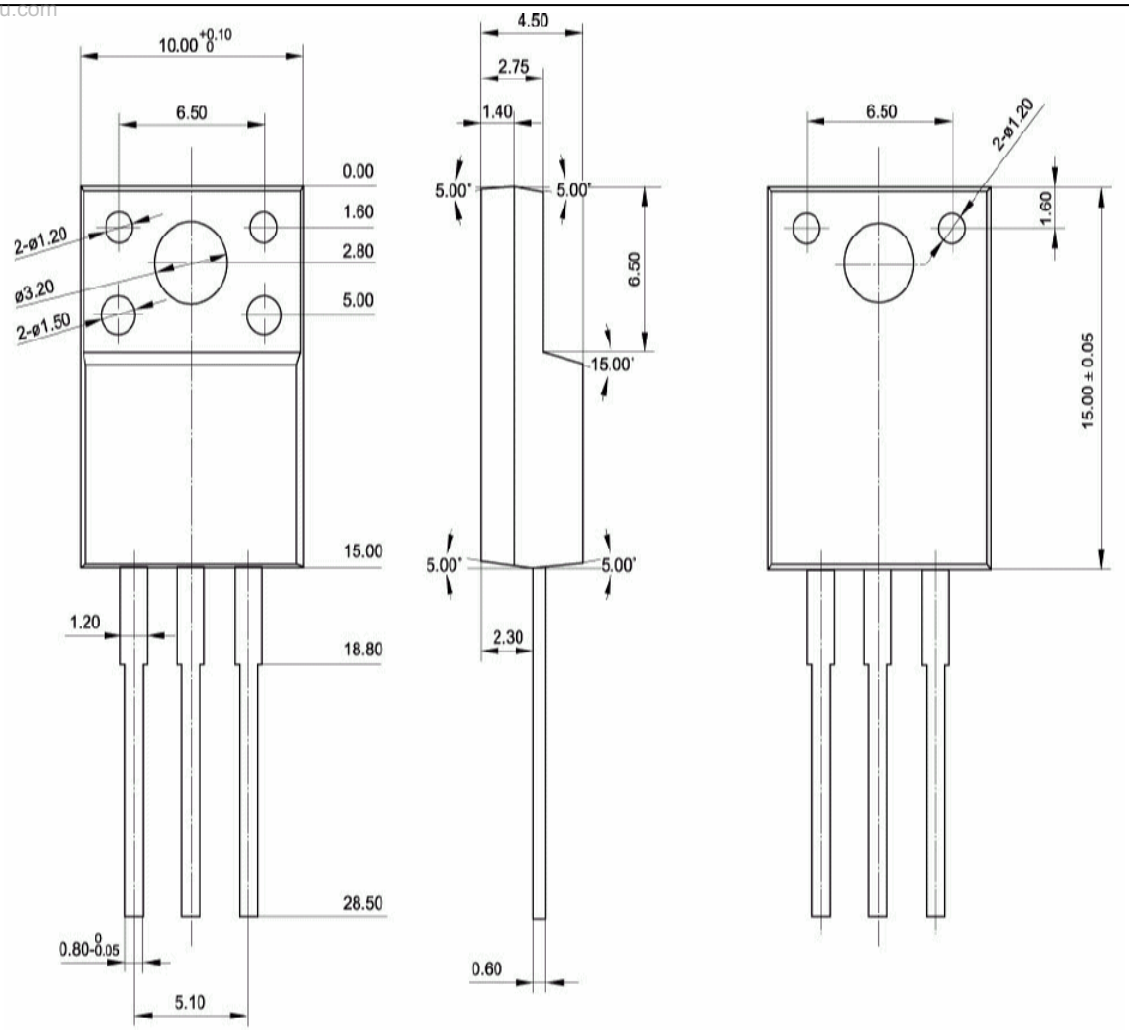

Fig.2 Outline dimensions (unindicated tolerance:±0.10 mm)

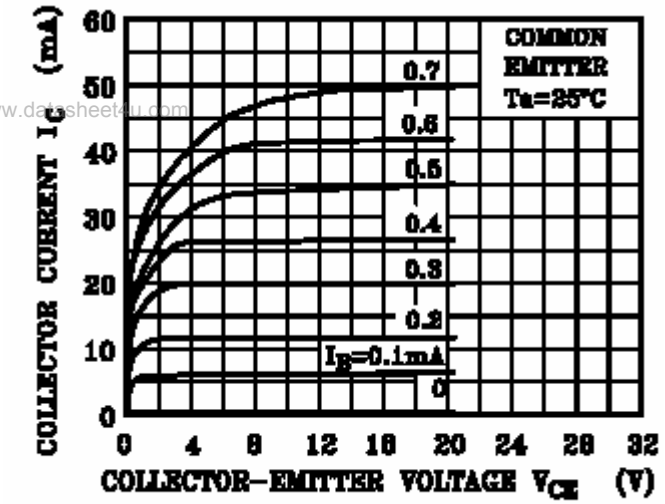

Fig.3 Static Characteristic

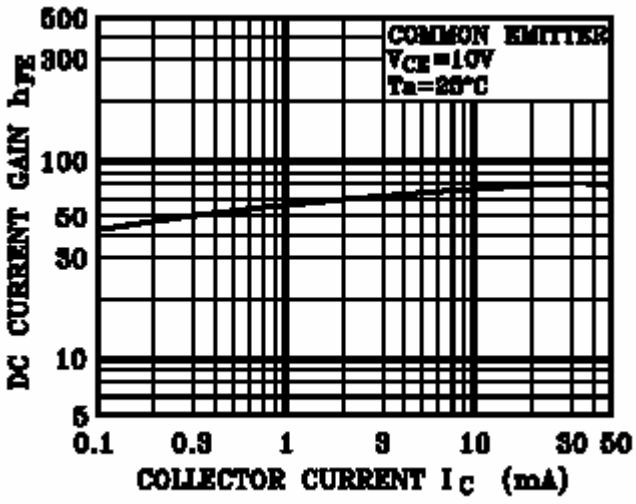

Fig.4 DC current Gain

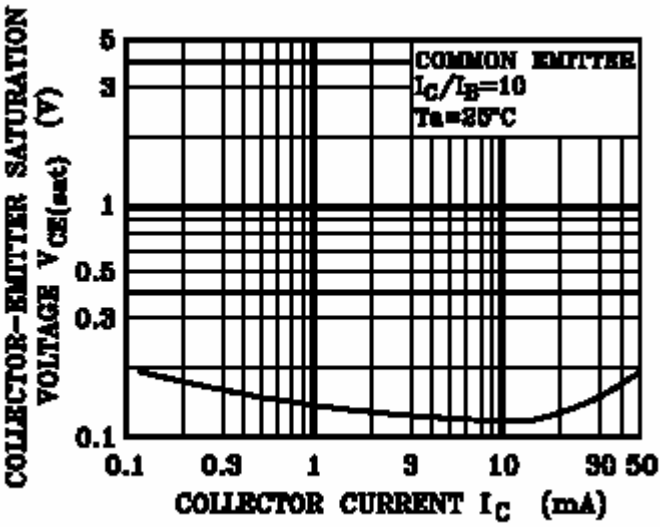

Fig.5 Collector-Emitter Saturation Voltage

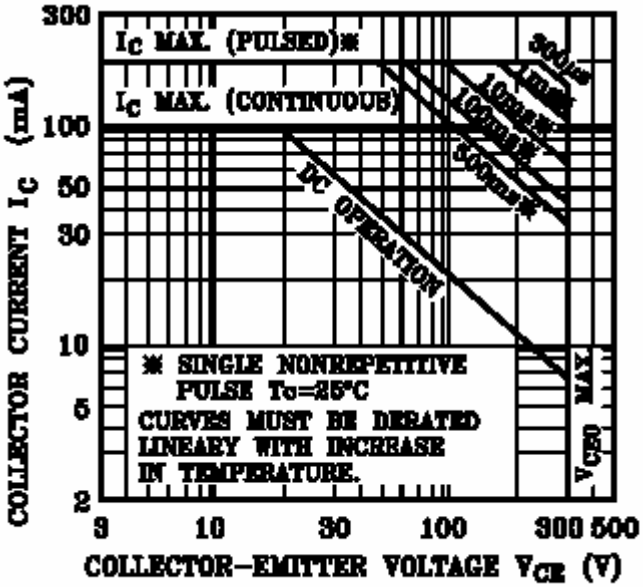

Fig.6 Safe Operating Area